TM05N03I N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

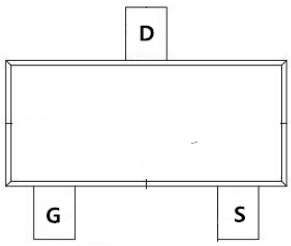
V_{DS} = 30V I_D =4.5A

$R_{DS(ON)}$ = 32mΩ(typ.) @ V_{GS}= 10V

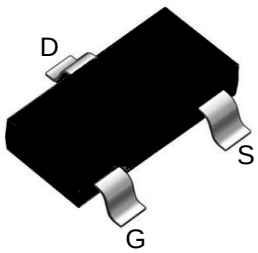
100% UIS Tested

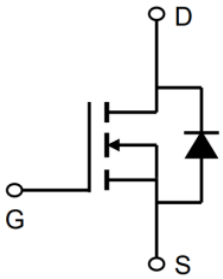
100% R_g Tested

Green Product



I:SOT-23





Marking:3400 OR A09T

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 4.5V[1]	4.5	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 4.5V[1]	2.8	A
I_{DM}	Pulsed Drain Current[2]	16.4	A
P_D@T_A=25℃	Total Power Dissipation[3]	1.1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	113	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	---	℃/W

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Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5	0.9	1.4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}=10V, I_D=4A	-	32	42	mΩ
		V_{GS}=4.5V, I_D=3A	-	36	48	
		V_{GS}=2.5V, I_D=2A	-	50	70	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz	-	285	-	pF
C_{oss}	Output Capacitance		-	33	-	pF
C_{rss}	Reverse Transfer Capacitance		-	27	-	pF
Q_g	Total Gate Charge	V_{DS}=15V, I_D=4A, V_{GS}=4.5V	-	2.6	-	nC
Q_{gs}	Gate-Source Charge		-	0.6	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	0.9	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V, I_D=2A, R_{GEN}=3Ω, V_{GS}=4.5V	-	15	-	ns
t_r	Turn-on Rise Time		-	42	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	16	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

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Typical Performance Characteristics

Figure1: Output Characteristics

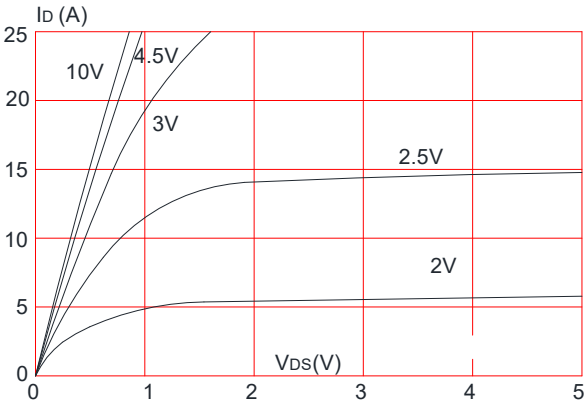

Figure 2: Typical Transfer Characteristics

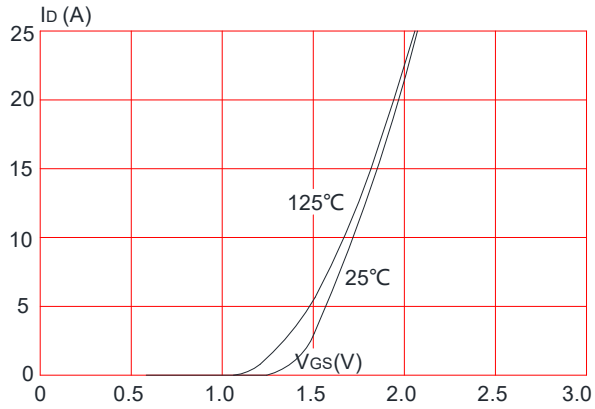

Figure 3: On-resistance vs. Drain Current

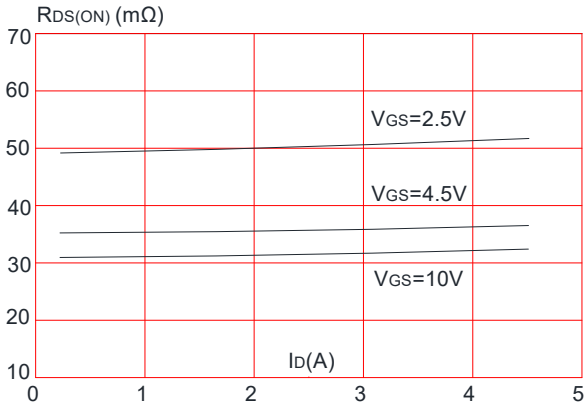

Figure 4: Body Diode Characteristics

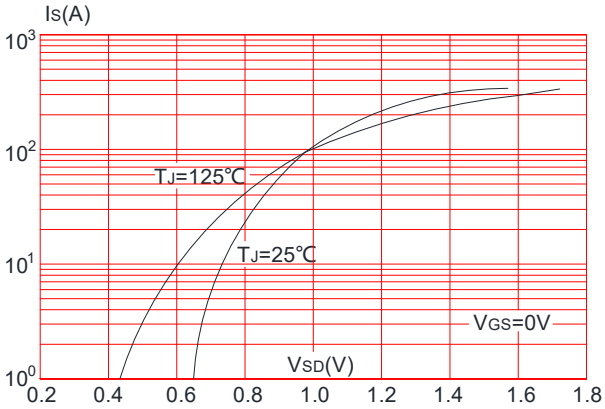

Figure 5: Gate Charge Characteristics

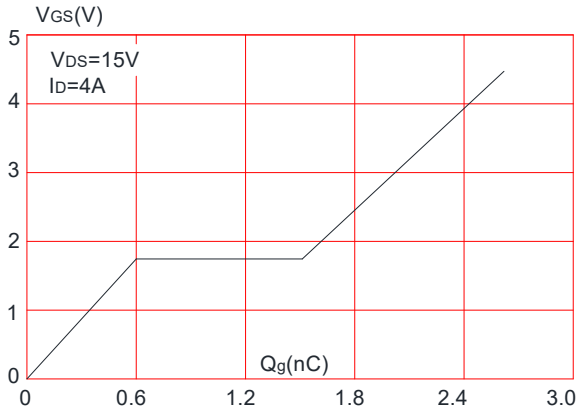

Figure 6: Capacitance Characteristics

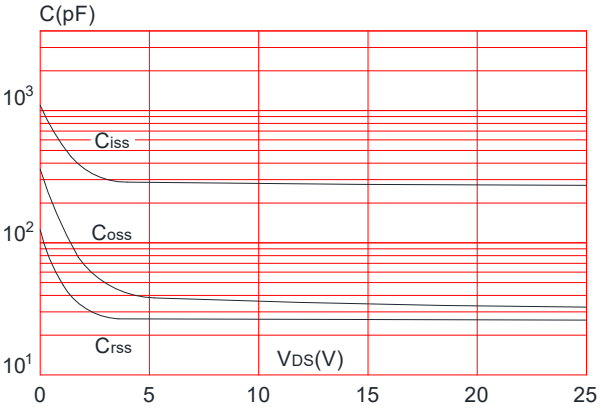

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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

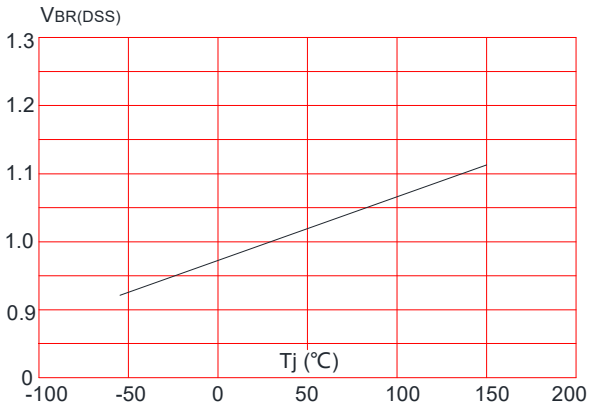


Figure 8: Normalized on Resistance vs. Junction Temperature

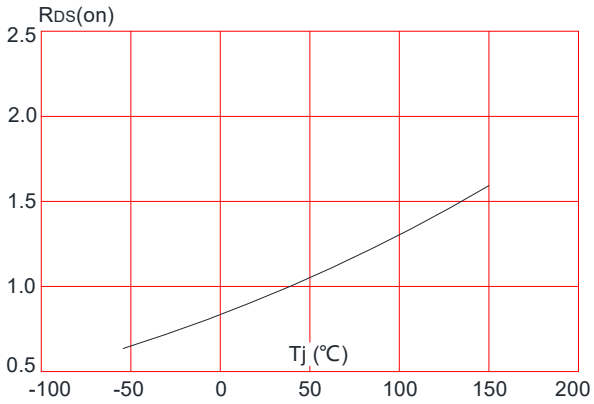


Figure 9: Maximum Safe Operating Area

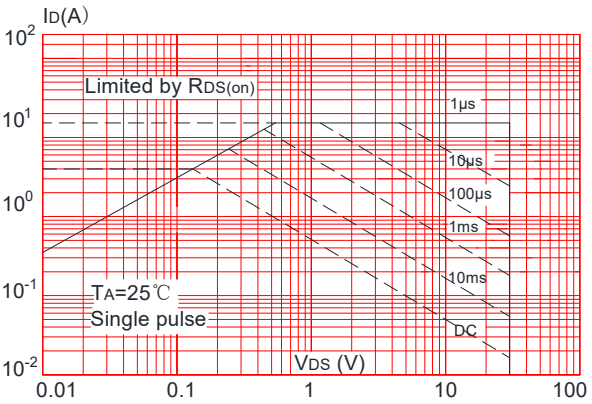


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

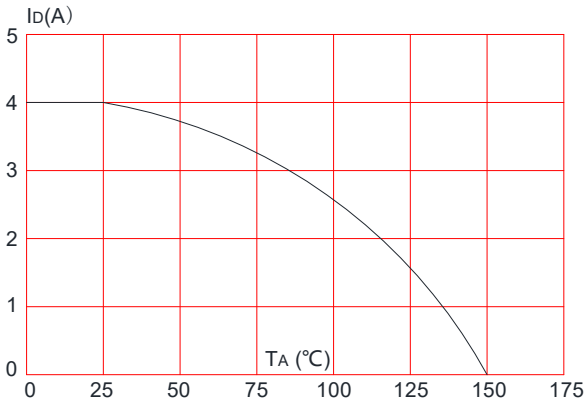
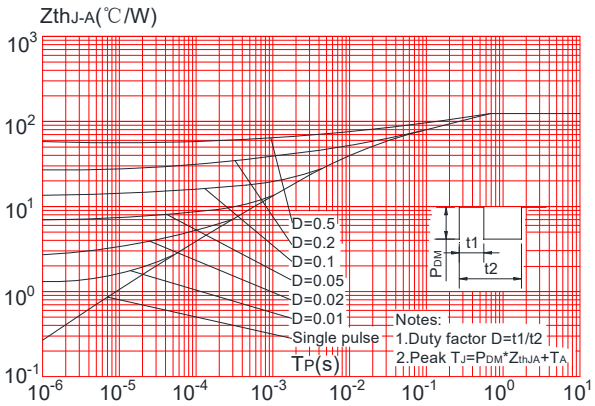


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



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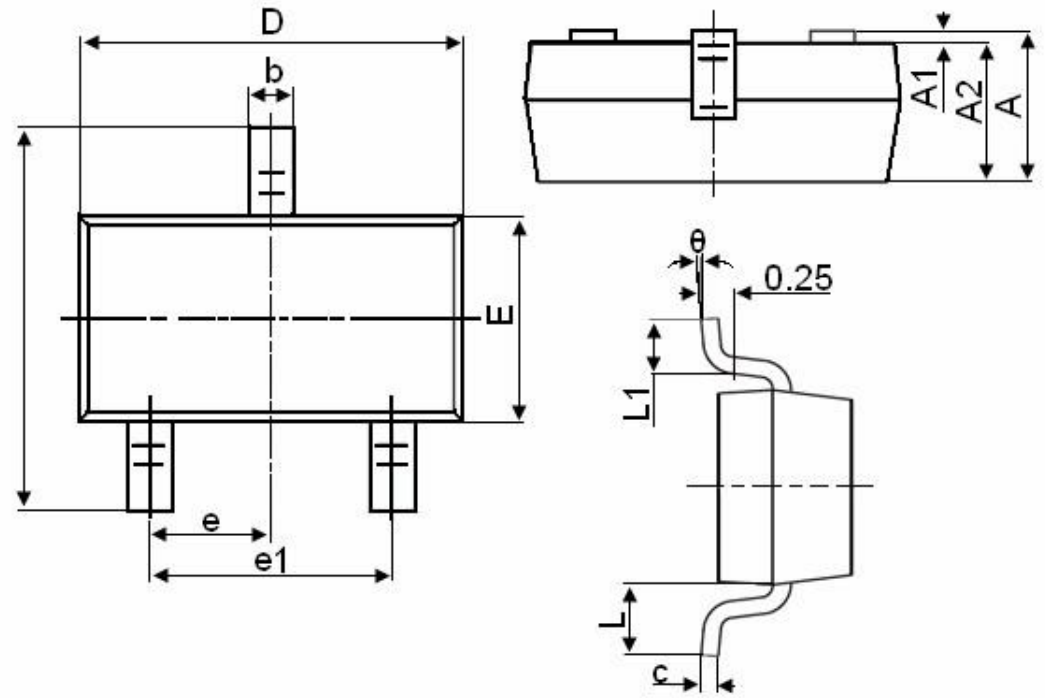
Package Information: SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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